

Product data sheet

## 1. General description

Ultrafast power diode in a SOD113 (2-lead TO-220F) plastic package.

### 2. Features and benefits

- Fast switching
- Isolated plastic package
- Low forward voltage drop
- Soft recovery characteristic

## 3. Applications

- Discontinuous Current Mode (DCM) Power Factor Correction (PFC)
- High frequency switched-mode power supplies

## 4. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>R</sub>	reverse voltage	DC		-	-	800	V
I <sub>F(AV)</sub>	average forward current	δ = 0.5 ; T <sub>h</sub> ≤ 73 °C; SQW; <u>Fig. 1</u> ; Fig. 2; Fig. 3	[1]	-	-	8	A
I <sub>FRM</sub>	repetitive peak forward current	$\delta$ = 0.5 ; t <sub>p</sub> = 25 µs; T <sub>h</sub> ≤ 73 °C; SQW		-	-	16	A
I <sub>FSM</sub>	non-repetitive peak forward current	t <sub>p</sub> = 10 ms; T <sub>j(init)</sub> = 25 °C; SIN		-	-	60	А
		t <sub>p</sub> = 8.3 ms; T <sub>j(init)</sub> = 25 °C; SIN		-	-	66	А
Static chara	acteristics	·					
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 8 A; T <sub>j</sub> = 150 °C; <u>Fig. 5</u>		-	1.07	1.5	V
		I <sub>F</sub> = 20 A; T <sub>j</sub> = 25 °C; <u>Fig. 5</u>		-	1.75	1.95	V
		I <sub>F</sub> = 8 A; T <sub>j</sub> = 25 °C		-	-	1.7	V
Dynamic ch	naracteristics	·					
t <sub>rr</sub>	reverse recovery time	I <sub>F</sub> = 1 A; V <sub>R</sub> = 30 V; dI <sub>F</sub> /dt = 100 A/μs; T <sub>i</sub> = 25 °C; <u>Fig. 6</u> ; <u>Fig. 7</u>		-	60	75	ns

[1] Neglecting switching and reverse current losses

# 5. Pinning information

Table 2. F	Pinning inf	formation		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	К	cathode	mb	K A
2	А	anode		001aaa020
mb	n.c.	mounting base; isolated	TO-220F (SOD113)	

# 6. Ordering information

Table 3. Ordering information							
Type number	Package						
	Name	Description	Version				
BYR29X-800	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 2-lead TO-220 "full pack"	SOD113				

## 7. Limiting values

#### Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Мах	Unit
V <sub>RRM</sub>	repetitive peak reverse voltage			-	800	V
V <sub>RWM</sub>	crest working reverse voltage			-	800	V
V <sub>R</sub>	reverse voltage	DC		-	800	V
I <sub>F(AV)</sub>	average forward current	$\delta$ = 0.5 ; T <sub>h</sub> ≤ 73 °C; SQW; <u>Fig. 1</u> ; <u>Fig. 2</u> ; <u>Fig. 3</u>	[1]	-	8	A
I <sub>FRM</sub>	repetitive peak forward current	$\delta$ = 0.5 ; t <sub>p</sub> = 25 µs; T <sub>h</sub> ≤ 73 °C; SQW		-	16	A
I <sub>FSM</sub>	non-repetitive peak	t <sub>p</sub> = 10 ms; T <sub>j(init)</sub> = 25 °C; SIN		-	60	А
	forward current	t <sub>p</sub> = 8.3 ms; T <sub>j(init)</sub> = 25 °C; SIN		-	66	А
T <sub>stg</sub>	storage temperature			-40	150	°C
Tj	junction temperature			-	150	°C

[1] Neglecting switching and reverse current losses

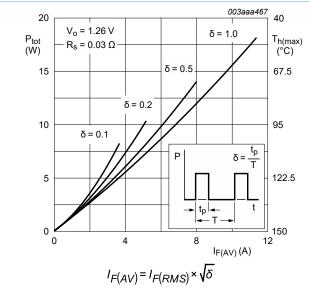


Fig. 1. Forward power dissipation and permissible heatsink temperature as a function of average forward current; square waveform; maximum values

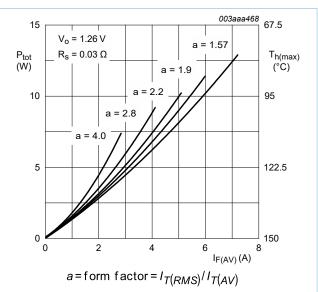
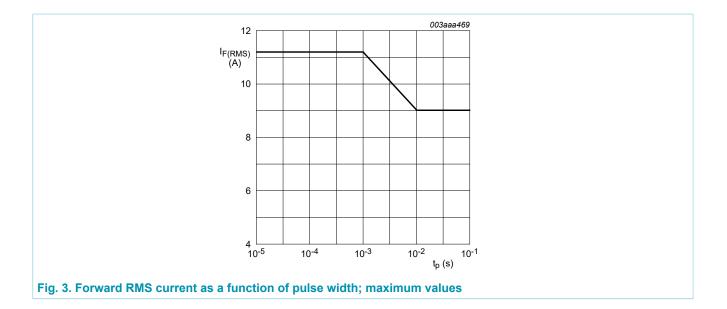


Fig. 2. Forward power dissipation and permissible heatsink temperature as a function of average forward current; sinusoidal waveform; maximum values

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# **BYR29X-800**

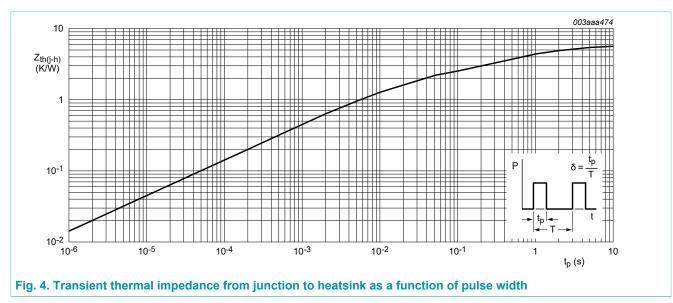
### Ultrafast power diode



Ultrafast power diode

### 8. Thermal characteristics

Table 5. Therma	al characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-h)</sub>	thermal resistance from junction to heatsink	with heatsink compound; Fig. 4	-	-	5.5	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient free air	in free air	-	55	-	K/W



## 9. Isolation characteristics

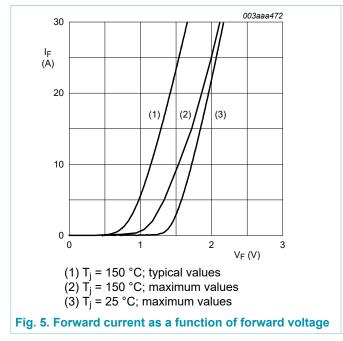
Table 6. Isolation characteristics							
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>isol(RMS)</sub>	RMS isolation voltage	50 Hz $\leq$ f $\leq$ 60 Hz; RH $\leq$ 65 %; from all pins to external heatsink; sinusoidal waveform; clean and dust free		-	-	2500	V
C <sub>isol</sub>	isolation capacitance	from cathode to external heatsink		-	10	-	pF

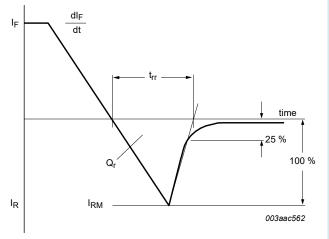
Table 5. Thermal characteristics

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### **10. Characteristics**

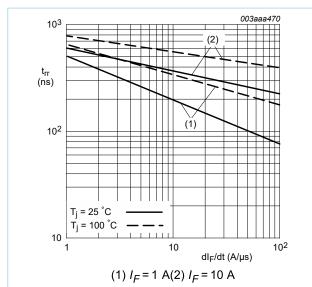
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics		· · · · · ·			
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 8 A; T <sub>j</sub> = 150 °C; <u>Fig. 5</u>	-	1.07	1.5	V
		I <sub>F</sub> = 20 A; T <sub>j</sub> = 25 °C; <u>Fig. 5</u>	-	1.75	1.95	V
		I <sub>F</sub> = 8 A; T <sub>j</sub> = 25 °C	-	-	1.7	V
I <sub>R</sub>	reverse current	V <sub>R</sub> = 800 V; T <sub>j</sub> = 25 °C	-	1	10	μA
		V <sub>R</sub> = 800 V; T <sub>j</sub> = 100 °C	-	0.1	0.2	mA
Dynamic ch	naracteristics					
t <sub>rr</sub>	reverse recovery time	$I_F = 1 \text{ A}; \text{ V}_R = 30 \text{ V}; \text{ d}I_F/\text{d}t = 100 \text{ A}/\mu\text{s}; T_j = 25 \text{ °C}; \text{ Fig. 6}; \text{ Fig. 7}$	-	60	75	ns
I <sub>RM</sub>	peak reverse recovery current	$ I_F = 10 \text{ A}; \text{ V}_R = 30 \text{ V}; \text{ d}I_F/\text{d}t = 50 \text{ A}/\mu\text{s}; \\ T_j = 100 \ ^\circ\text{C}; \ \underline{\text{Fig. 6}}; \ \underline{\text{Fig. 8}} $	-	-	6	A
Q <sub>r</sub>	recovered charge	$I_F = 2 \text{ A}; \text{ V}_R = 30 \text{ V}; \text{ d}I_F/\text{d}t = 20 \text{ A/s}; T_j = 25 °C; Fig. 9; Fig. 6$	-	150	200	nC
V <sub>FR</sub>	forward recovery voltage	I <sub>F</sub> = 10 A; dI <sub>F</sub> /dt = 10 A/μs; T <sub>j</sub> = 25 °C; Fig. 10	-	5	-	V







### Ultrafast power diode





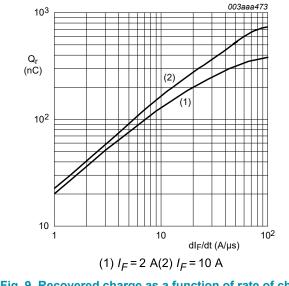
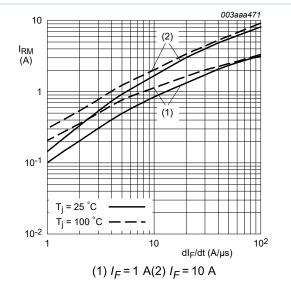
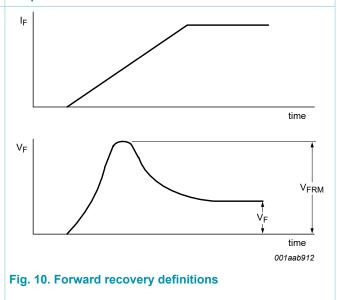


Fig. 9. Recovered charge as a function of rate of change of forward current



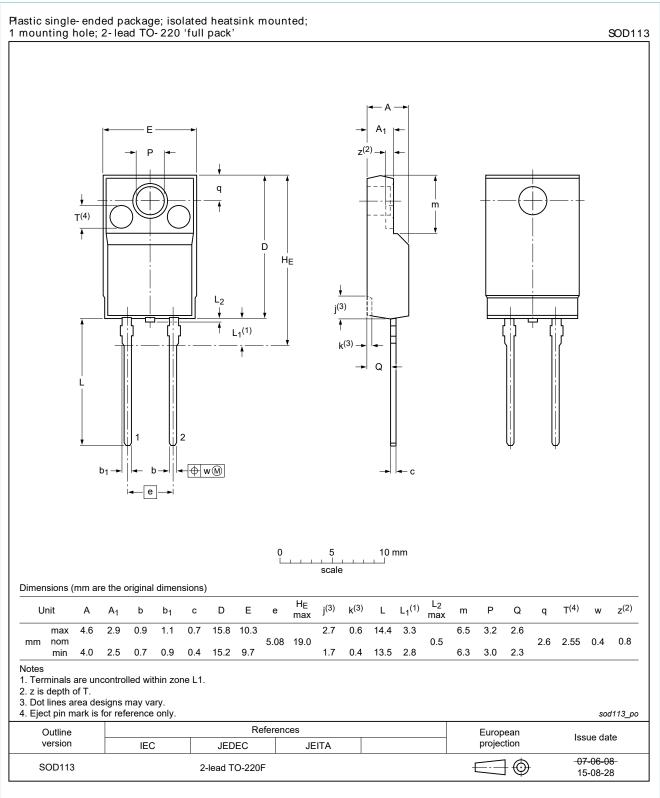






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### **11. Package outline**



### Fig. 11. Package outline TO-220F (SOD113)

BYR29X-800

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## 12. Legal information

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Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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